



Testbeam and laboratory test results of irradiated 3D CMS pixel detectors

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The CMS experiment





The CMS Pixel Detector







- Barrel layers at r of 4.3,7.3,10.4 cm
- Forward disks at z of ±34.5, ±46.5 cm (modules tilted 20° for better resolution)
- High granularity: 66 MPix camera
 - $-100 \ \mu m \ x \ 150 \ \mu m$ pixel dimensions
- Low mass occupancy
- 1 m² silicon coverage

3D vs planar technology



- p+ and n+ electrodes are arrays of columns that penetrate into the bulk
- Lateral depletion and charge collection is sideways
- Superior radiation hardness due to smaller electrode spacing:
 - smaller carrier drift distance
 - faster charge collection
 - less carrier trapping
 - lower depletion voltage

Disadvantages:

- Higher noise
- Complex, non-standard processing



E. Alagoz, VCI 2013, Vienna



3D @ CERN LHC



3Ds are promising tracking detector candidates for future upgrades at LHC

25% of ATLAS IBL will be 3D sensors at phase I upgrade in 2015



- New rad-hard sensor candidates for the HL-LHC CMS vertex detector (L = 10³⁵cm⁻²s⁻¹)
- Equivalent dose ~ $10^{16}n_{eq}/cm^2$ @ r = 5 cm
- Current CMS pixel detector can collect 50% charge at the fluence of ~ 1x10¹⁵n_{eq}/cm² at >= 600V (doi:10.1016/j.nima.2010.03.157)



HPS (near beam proton spectrometer - under approval for CMS)

Crucial requirement for this application: radiation hardness and active edges



3D layouts (200 µm substrate thickness)





3D sensor assembly



- 3D sensors bump-bonded to CMS PSI46v2 readout chip
 - At IZM for SINTEF 3Ds (PbSn)
 - At SELEX for FBK 3Ds (In)
 - At IZM for CNM 3Ds (PbSn)
- CMS sensor dimensions $52(col)x80(row) (100 \ \mu m \ x \ 150 \ \mu m)$
- Wire bonding and assembly done at Purdue, FNAL, and Torino
- *Purdue flip-chip bonder* fully functional for next 3D sensors

Lab testing:

- ROC calibration
- Leakage current
- Noise
- Radioactive source testing





CMS 3D sensor assembly









Noise measurements





Source charge collection







- Irradiation at the Los Alamos Neutron Science Center (LANSCE) with 800 MeV protons/cm²
 - Fluences: 5E14, 1E15, and 5E15 p/cm² (FBK)
 - Fluences: 1E15, and 5E15 p/cm² (SINTEF)
 - Fluences: 1E14, 3E14, 5E14, and 1E15 p/cm² (CNM)
- Post-irradiation lab (@ Purdue) and beam tests (@ FNAL) performed for SINTEF and FBK 3D sensors
 - CNM sensors only tested in testbeams
- Most of the readout chips work after irradiation
 - Except SINTEF case: 1 out of 6 ROCs worked, and CNM sensors had calibration problems
- Post-irradiation lab measurements carried out in the thermal chamber running at -20 °C
 - sensor temp estimated by an IR camera to be -7 $^{\circ}$ C

800 MeV proton to 1 MeV neutron equivalent conversion factor is 0.7

Post-irradiation charge collection





Fermilab testbeam setup





Beam test: pre-irradiation





Beam tests: pre-irradiation





Beam test: post-irradiation





- Measured at -20 °C
- No tilt (0° degree) wrt beam
- Electrodes are less sensitive: observed lower efficiency in electrode regions
- Simulations ongoing to understand post-irradiation sensor efficiencies

Beam test: post-irradiation





Efficiency at maximum bias

Sensor	Pre-irradiation	Post-irradiation	Fluence [n _{eq} /cm ²]
1E_1	97.7	37.9	3.5 10 ¹⁵
1E_2	81.1	59.2	0.7 10 ¹⁵
2 E	97.1	91.1	0.7 10 ¹⁵

New improved 3D sensors

• WAFER LAYOUT:

- ATLAS10 batch
- CMS-1E diode only
- Diodes are highlighted (RED)
- The shipped test structures are also highlighted (ORANGE)

• Test structures (TestPad):

- Gate controlled diode
- MOS capacitor
- Planar diode
- Capacitor

CM 1E diodes:

- 3.5x3.8 mm2
- 200 +- 20 um thickness
- 19x29 pixel arrays









Diodes pre- and post-cut IV measurements



Temperature range: 0 °C- 20 °C



Diodes irradiated while actively biased (-10V)

Breakdown improved from -40 V to -80 V

Capacitance measurements







• ~200 pF at -10 V



2.26 MRad (Gamma irradiation facility at Purdue)

- Post-irradiation full depletion
 ~ -20 V at 20 °C
- ~200 pF at -10 V

Summary & outlook



- 3D sensors have several features outperform planar sensors
- Sensors received from SINTEF (Norway), FBK (Ital), and CNM (Spain)-
- Breakdown voltage: SINTEF > 100V, CNM > 100V, and FBK <= 40V
- 3D sensors have higher noises
- Pre-irradiation beam test results show efficiencies higher than 90%
- Irradiated fluences are between 1E14 and 3.5x10¹⁵ n_{eq}/cm² (800 MeV protons)
- Beam tests at Fermilab
 - > 90% tracking efficiency before irradiation
 - Low tracking efficiency after irradiation due
 - High readout threshold
 - Low electric field (lower post-irradiation breakdown voltage)
 - Good charge collection after heavy irradiation wrt planar
 - 2E configuration outperforms 1E and 4E after irradiation
- Expecting more 3Ds from SINTEF, FBK and CNM
- Ongoing simulation to develop understanding FBK beam test results
- New irradiation fluences up to 1E16 n_{eq}/cm²

CMS 3D collaboration







Czech Technical University, Fermilab, Purdue University, INFN Torino, SINTEF, SLAC, University of Hawaii, University of Manchester







